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| | B2 | 0 514 018 | 11/19/1992 | EP | | | | No | Yes |
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| | B7 | 0 838 858 | 04/29/1998 | EP | | | | No | No |

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| FORM PTO – 1449<br>INFORMATION DISCLOSURE STATEMENT<br>COPY | ATTY DOCKET NO.: | ASC-025DV2C1 |
|---|---|---|
| | APPLICANTS: | Cheng *et al.* |
| | SERIAL NO.: | 10/802,186 |
| | FILING DATE: | March 17, 2004 |
| | GROUP: | Not yet assigned |

OTHER ART, JOURNAL ARTICLES, ETC.

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